

Re-entrant Coulomb Drag Between Vertically-Coupled Quantum Wires

Sandia National Laboratories is a multi-program laboratory managed and operated by Sandia Corporation, a wholly owned subsidiary of Lockheed Martin Corporation, for the U.S. Department of Energy's National Nuclear Security Administration under contract DE-

SAND2011-5908 C

Dominique Laroche^{1,2}, John L. Reno¹, Guillaume Gervais² and Michael P. Lilly¹

SAND2011-5908C

¹ Center for Integrated Nanotechnologies, Sandia National Laboratories, Albuquerque, United States ² Department of Physics, McGill University, Montréal, Canada

Motivation

Goal : Study electron interactions between 1 dimensional systems coupled at the nanoscale

- Address the wires multiple 1D subbands regime
- Study one-dimensional electron-hole asymmetry
- Ultimately investigate Luttinger liquid theory

Tool : Coulomb Drag measurement

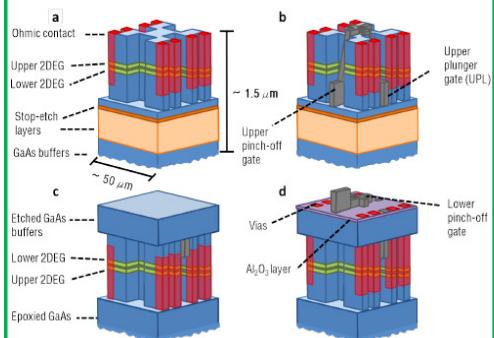
- Direct probe of electron-electron interactions

How : Independent and vertically-coupled quantum wires

Device fabrication

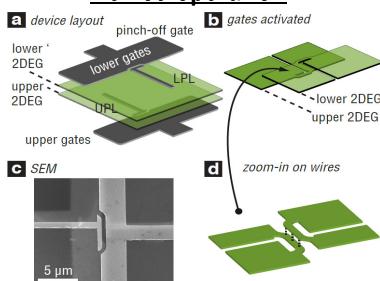
Start with double quantum well GaAs/AlGaAs heterostructure with double stop-etch layer.

- 18 nm wide quantum wires.
- Density of $1.1 (1.4) \times 10^{11} \text{ cm}^{-2}$ for the lower (upper) layer and combined mobility of $4.0 \times 10^5 \text{ cm}^2 / \text{V} \cdot \text{s}$.



- Defining the mesa, and depositing and annealing ohmic contacts.
- Defining the upper gates, using a combination of both photo and e-beam lithography.
- Performing an Epoxy-Bond-And-Stop-Etch (EBASE) technique [1], which consists of gluing bare GaAs on top of the device and flipping it, then etching the original substrate until the lower 2DEG is ~ 150 nm away from the surface.
- Depositing an insulating Al_2O_3 layer and defining the lower gates, which are now on top of the device.

Device operation



Advantages of design :

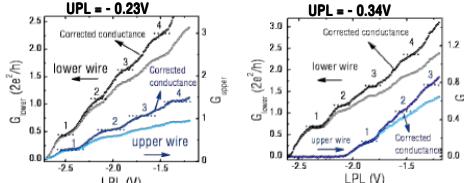
- Independent ohmic contacts, with suitable bias on gates
 - Probe both wires independently
- Independent control of 1D subbands occupancy in each wire
 - Easy to study multiple and single 1D subbands regimes
- Hard MBE-defined barrier between the wires
 - Fixed interwire separation
 - Interwire separation in the 10's nm range possible
 - Regime where Coulomb drag dominates
 - Stronger drag signal
 - Stronger interwire many-body interactions

Current wire properties :

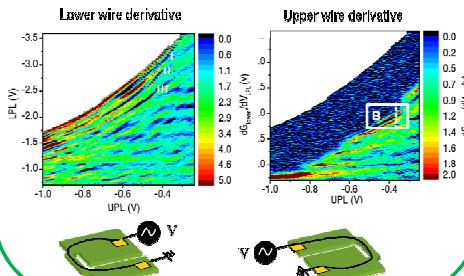
- $4.2 \mu\text{m}$ long wires
- Barrier of 15 nm between both wires
- Effective center-to-center interwire separation ≤ 41 nm

Wires characterization

- The plunger gates are coupled to both wires
 - Sweeping a single gate affects both wires
- Non-ballistic wires are observed
 - $G < 2e^2/h \times N$; N = number of 1D subbands
- After subtracting series resistance, approximately even spacing between steps is observed
- Consistent with non-ballistic 1D subbands [2]
- Similar (UPL = -0.23V) and different (UPL = -0.34V) subband occupancy can be achieved.

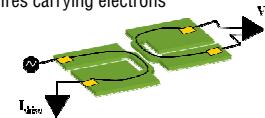


- A complete mapping of the wires conductance can be performed as a function of UPL (upper plunger) and LPL (lower plunger)
- The wire's features are more apparent in the derivative
 - 1D subbands appear as black and blue stripes
- 1D subbands can be tracked over the whole gate voltage range.



Coulomb drag basics

- Coulomb drag is a direct probe of electron-electron interactions.
- Send a current I_{drive} in one wire
- Measure the resulting voltage drop V_{drag} in the other wire
 - No current flow allowed in the drag wire
- Measured quantity is the transresistance
 - $R_D = \frac{-V_d}{I}$
- Theory predicts a positive drag between two one dimensional wires carrying electrons



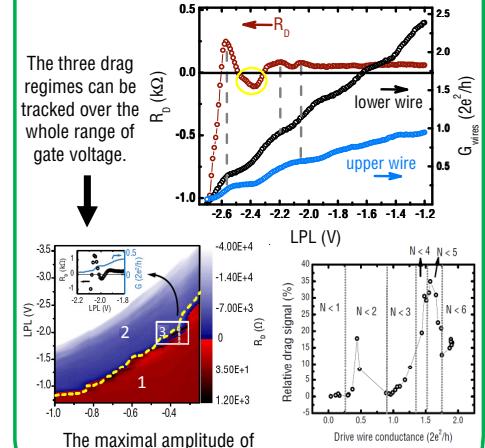
Main results

3 regimes are observed in the Coulomb drag measurement

- 1- Positive drag : Peaks are observed as 1D subbands open in either wire (dotted gray lines)
 - Previously observed by Debray *et. al.* [3] and predicted from electron-hole asymmetry [4].

- 2- Low-density negative Coulomb drag : occurs at highly negative LPL values
 - Previously observed by Yamamoto *et. al.* [2] in similar conditions but in the presence of a magnetic field.
 - Was attributed to Wigner crystallization

- 3 – High-density re-entrant negative Coulomb drag (yellow circle)
 - Never observed previously
 - Is inconsistent with Wigner crystallization
 - Might be caused by a non-monotonic in the wires transmission probability coupled with electron-hole asymmetry or by a local hole-like dispersion relation in the quantum wires band structure.



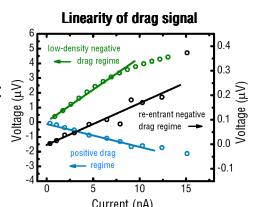
The maximal amplitude of the drag signal can reach up to 35 % of the drive signal.

Coulomb drag tests

Several tests were performed to insure that the signal observed was truly Coulomb drag.

- 1- V_{drag} is linear with I_{drive} for small enough excitation
 - $eV_{\text{drive}} \lesssim 3 \text{ K}$
 - True for all three regimes:

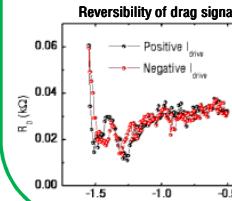
- positive regime
- high-density negative regime
- low-density negative regime



- 2- R_{drag} is independent of I_{drive} direction

- 3 – R_{drag} is independent of frequency

- 4 – No DC signal is observed in the drag wire when an AC I_{drive} is sent through the drive wire.



Conclusion

Summary :

- Fabricated the first vertically-coupled quantum wires suitable for Coulomb drag measurements
- Measured Coulomb drag and observed both positive and negative regimes
- Observed new re-entrant negative drag which is inconsistent with Wigner crystallization and ill-understood at the moment

Future directions : Study temperature dependence of Coulomb drag

- Understand origin of negative Coulomb drag
- Study Luttinger liquid physics

References

- [1] Weckwerth, M. V. *et al.* Superlatt. Microstruct. **20**, 561 (1996)
- [2] Auslaender, O. M., *et al.* Phys. Rev. Lett **84**, 1764 (2000)
- [3] Debray, P. *et al.*, J. Phys. Condens. Matter **13**, 3389 (2001)
- [4] Levchenko, A. and Kamenev, A. Phys. Rev. Lett. **101**, 216806 (2008)
- [5] Yamamoto, M. *et al.*, Science, **313**, 204 (2006)